Remarks

The Examiner had rejected the previous claims under 35 U.S.C. §103(a) as unpatentable

over Pu et al. U.S. Patent No. 6,825,618 in view of Brcka U.S. Patent Publication

No. 2001/0022158, some further in view of Davis et al. U.S. Patent No. 6,685,799, and others

still further in view of Todorov et al. U.S. Patent Publication No. 2003/0006009.

With the new claims, Applicants has rearranged the elements and expanded on the

relationships between the elements and the functions of the subject matter in a way that should

make it easier to appreciate novelty and unobviousness of the claimed invention.

It is recognized that, in semiconductor processing and related technologies, everyone

seeks to achieve uniformity of the process at the wafer level. In plasma processing, almost

everyone seeks to achieve process uniformity on the wafer with a plasma source that produces

uniform plasma. Applicants takes a course that is different, by providing a peripheral ionization

source that produces a plasma having an annular, alternating, high and low power distribution.

Applicant does this by providing the source with a segmented configuration of alternating high-

radiation and low-radiation segments arranged in a ring and positioned to couple power through

a dielectric chamber wall into the chamber. No prior art reference seeks to achieve this.

More particularly, Applicants peripheral ionization source includes an RF antenna on the

atmospheric side of a dielectric chamber wall and a shield on the vacuum side of the dielectric

chamber wall. The shield has alternating high-transparency and low-transparency sections

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arranged in a ring and positioned relative to the antenna to facilitate the coupling of RF

energy from the antenna through the dielectric chamber wall and the shield and into the

chamber in the annular, alternating, high and low power distribution. The high-radiation

segments include the high-transparency sections of the shield and the low-radiation segments

include the low-transparency sections of the shield.

More specifically, the high-transparency sections of the shield each have a plurality

of slots therethrough that are oriented relative to the antenna to facilitate inductive coupling

through the high-transparency shield sections. The low-transparency sections of the shield

are electrically conductive and substantially more solid than the high-transparency sections

to impede inductive coupling through the low-transparency sections of the shield.

No combination of references provides a sectioned shield that contributes to a

segmented configuration in a peripheral source having alternating high-radiation and low-

radiation segments arranged in a ring and designed to produce an annular, alternating, high

and low power distribution plasma. To produce a plasma with such a power distribution

would do what the references seek to avoid, thereby deterring those in the art from combining

and modifying references in such a way.

Applicants also include, by way of dependent claims, antennas having segmented

configurations that include high-efficiency sections that provide concentrated antenna current

paths close to the dielectric chamber wall and low-efficiency sections that provide distributed

antenna current paths. This produces stronger magnetic fields adjacent the high-efficiency

sections of the conductor and weaker magnetic fields adjacent the low-efficiency sections of

the conductor. By aligning the high-efficiency sections of the antenna with the high-

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> transparency sections of the shield, the high-radiation and low-radiation segments of the peripheral ionization source are produced in an effective way.

> It is submitted that the claims, as amended are patentable. Accordingly, allowance is respectfully requested.

If any further charges are necessary, please apply them to Deposit Account 23-3000.

Respectfully submitted,

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